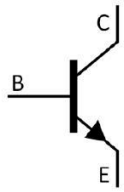
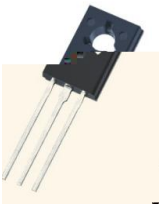
TO-126 NPN Silicon NPN transistor in a TO-126 Plastic Package.

P_C=1.5W Ta=25

High Power Dissipation :P_C=1.5W(Ta=25).

Low collector saturation voltage ,large current.





PIN1 Emitter PIN 2 Collector PIN 3 Base

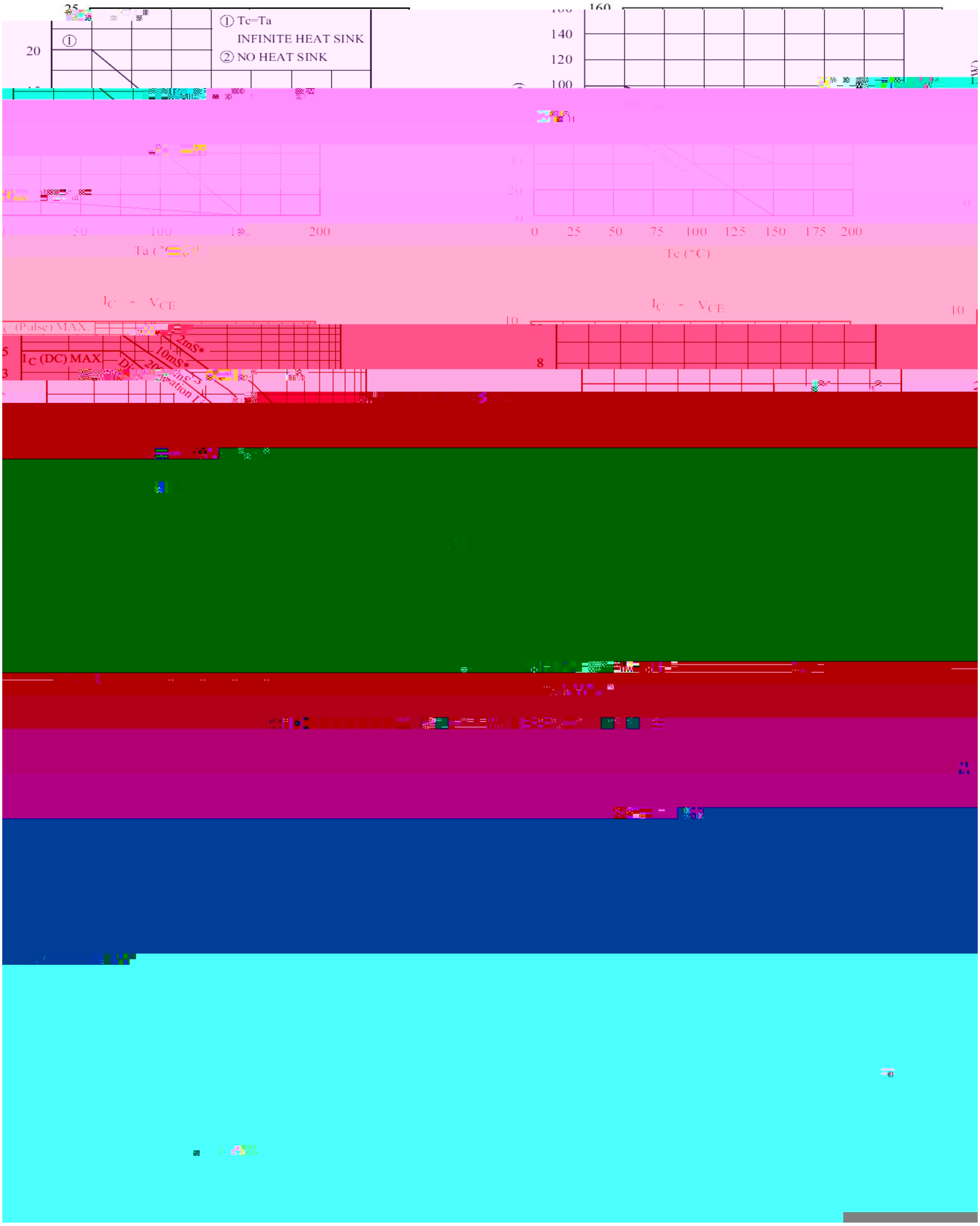
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	5.0	A
Peak Collector Current	I_{CP}	8.0	A
Base Current - Continuous	I_B	1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	P_C(Tc=25)	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CB}=50V I_E=0			10	A
Emitter Cut-off Current	I_{EBO}	V_{EB}=7V I_C=0			10	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=2.0A	100		400	
	$h_{FE(2)}$	V_{CE}=1.0V I_C=0.1A	60			
	$h_{FE(3)}$	V_{CE}=2.0V I_C=5.0A	50			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=0.2A		0.1	0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=2.0A I_B=0.2A		0.9	1.2	V
Turn On Time	t_{on}	V_{CC}=10V I_B=0.2A		0.2	1	s
Fall Time	t_f			1.1	2.5	s
Storage Time	t_S			0.2	1	s

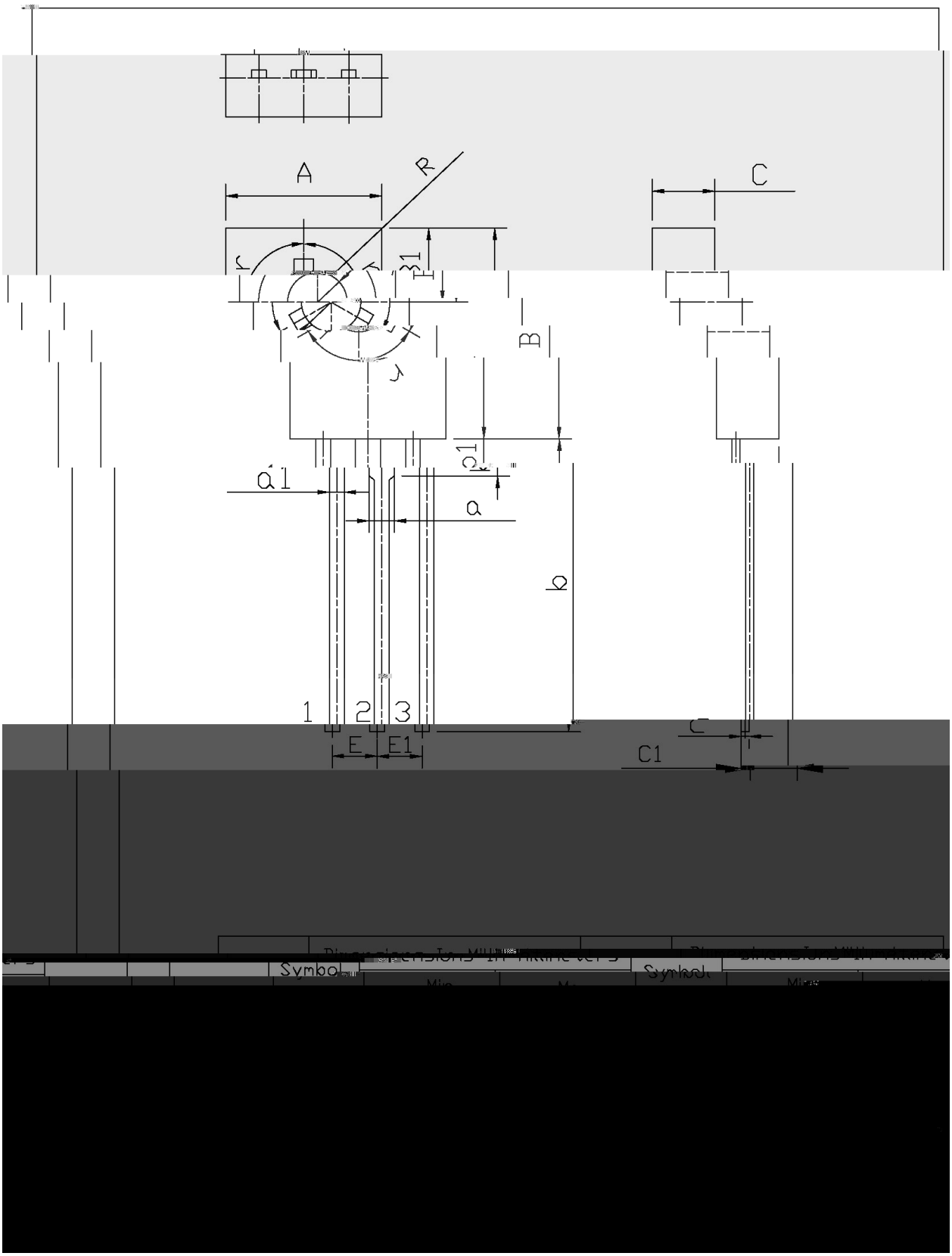
Pc - Ta

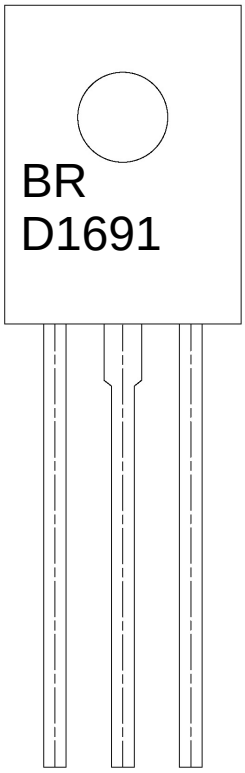
d_T - T_C


① Tc=Ta
INFINITE HEAT SINK
② NO HEAT SINK
Ta (°C)
Tc (°C)
I_C - V_{CE}
I_C - V_{CE}
IC (DC) MAX
2mS*
10mS*

TO-126

单位：mm





BR

D1691

****

Note:

BR:	Company Code
D1691:	Product Type.
****:	Lot No. Code, code change with Lot No.

		Note:	
1	25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2	255±5 5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱